

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD090P** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.5 A PEAK
V_{CB}	55 V
P_{DISS}	250 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.6 °C/W

PACKAGE STYLE .280 4L PILL (A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

ORDER CODE: ASI10563

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10\text{ mA}$	65			V
BV_{CER}	$I_C = 10\text{ mA}$ $R_{BE} = 10\ \Omega$	65			V
BV_{EBO}	$I_E = 1\text{ mA}$	3.5			V
I_{CES}	$V_{CB} = 50\text{ V}$			6.25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		100	---
P_G	$V_{CC} = 50\text{ V}$ $P_{OUT} = 90\text{ W}$ $f = 1025 - 1150\text{ MHz}$	8.5			dB
η_C		35			%